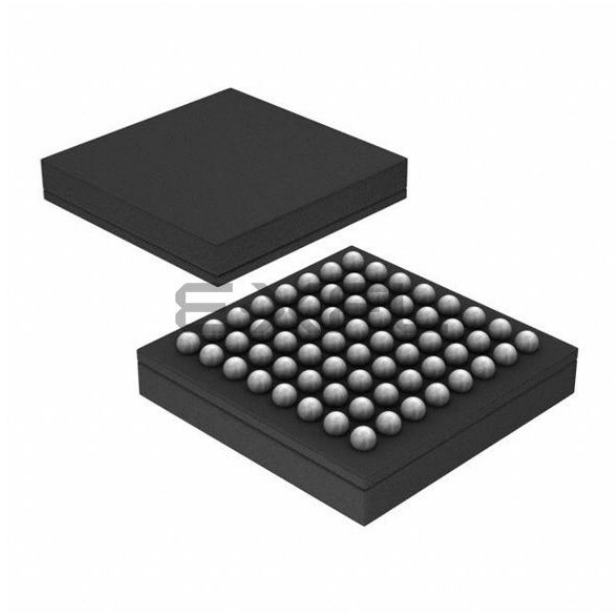

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 20x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TFBGA
Supplier Device Package	64-TFBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l152r6h6a

Contents

2 Description

The ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A devices incorporate the connectivity power of the universal serial bus (USB) with the high-performance ARM® Cortex®-M3 32-bit RISC core operating at a frequency of 32 MHz (33.3 DMIPS), a memory protection unit (MPU), high-speed embedded memories (Flash memory up to 128 Kbytes and RAM up to 32 Kbytes) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

All the devices offer a 12-bit ADC, 2 DACs and 2 ultra-low-power comparators, six general-purpose 16-bit timers and two basic timers, which can be used as time bases.

Moreover, the STM32L151x6/8/B-A and STM32L152x6/8/B-A devices contain standard and advanced communication interfaces: up to two I^2Cs and SPIs, three USARTs and a USB. The STM32L151x6/8/B-A and STM32L152x6/8/B-A devices offer up to 20 capacitive sensing channels to simply add touch sensing functionality to any application.

They also include a real-time clock with sub-second counting and a set of backup registers that remain powered in Standby mode.

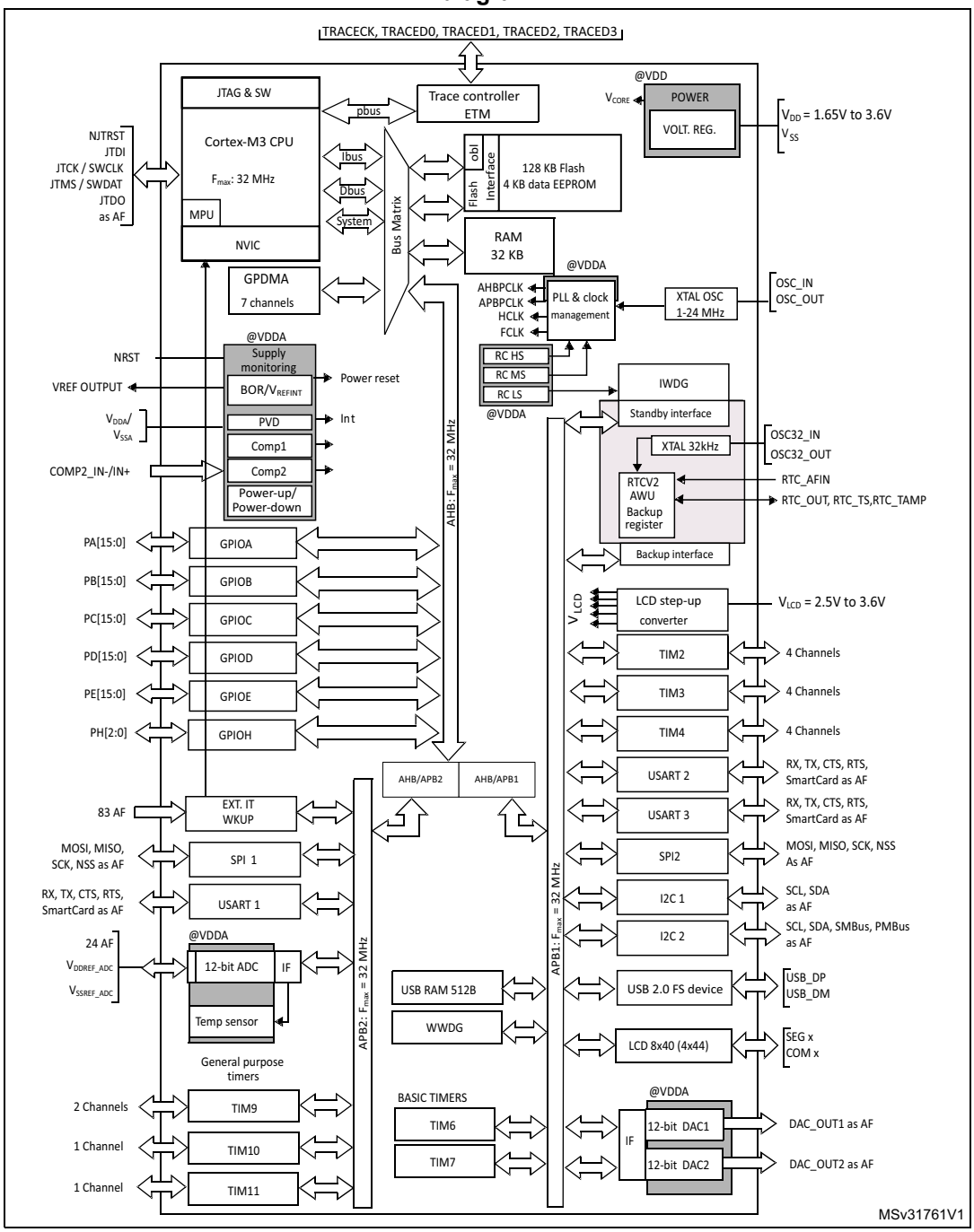
Finally, the integrated LCD controller (except STM32L151x6/8/B-A devices) has a built-in LCD voltage generator that allows to drive up to 8 multiplexed LCDs with contrast independent of the supply voltage.

The ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +85 °C and -40 to +105°C temperature ranges. A comprehensive set of power-saving modes allows the design of low-power applications.

3 Functional overview

Figure 1 shows the block diagram.

Figure 1. Ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A block diagram



1. AF = alternate function on I/O port pin.

line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB wakeup.

Stop mode consumption: refer to *Table 23*.

- **Standby** mode with RTC

  Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI RC and HSE crystal oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

  The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

- **Standby** mode without RTC

  Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI, RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

  The device exits Standby mode in 60 µs when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

  Standby mode consumption: refer to *Table 24*.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering the Stop or Standby mode.

Table 3. Functionalities depending on the operating power supply range

Operating power supply range	Functionalities depending on the operating power supply range			
	DAC and ADC operation	USB	Dynamic voltage scaling range	I/O operation
V_{DD} = 1.65 to 1.71 V	Not functional	Not functional	Range 2 or Range 3	Degraded speed performance
V_{DD}= 1.71 to 1.8 V (1)	Not functional	Not functional	Range 1, Range 2 or Range 3	Degraded speed performance
V_{DD} = 1.8 to 2.0 V(1)	Conversion time up to 500 Ksps	Not functional	Range 1, Range 2 or Range 3	Degraded speed performance

Table 5. Working mode-dependent functionalities (from Run/active down to standby) (continued)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
DAC	Y	Y	Y	Y	Y	-	-	-
Temperature sensor	Y	Y	Y	Y	Y	-	-	-
Comparators	Y	Y	Y	Y	Y	Y	-	-
16-bit Timers	Y	Y	Y	Y	-	-	-	-
IWDG	Y	Y	Y	Y	Y	Y	Y	Y
WWDG	Y	Y	Y	Y	-	-	-	-
Touch sensing	Y	-	-	-	-	-	-	-
Systick Timer	Y	Y	Y	Y	-	-	-	-
GPIOs	Y	Y	Y	Y	Y	Y	-	3 pins
Wakeup time to Run mode	0 µs	0.4 µs	3 µs	46 µs	< 8 µs		58 µs	
Consumption V_{DD}=1.8V to 3.6V (Typ)	Down to 185 µA/MHz (from Flash)	Down to 36.9 µA/MHz (from Flash)	Down to 10.9 µA	Down to 5.5 µA	0.43 µA (No RTC) V_{DD}=1.8 V		0.27 µA (No RTC) V_{DD}=1.8 V	
					1.13 µA (with RTC) V_{DD}=1.8 V		0.87 µA (with RTC) V_{DD}=1.8 V	
					0.44 µA (No RTC) V_{DD}=3.0 V		0.28 µA (No RTC) V_{DD}=3.0 V	
					1.38 µA (with RTC) V_{DD}=3.0 V		1.11 µA (with RTC) V_{DD}=3.0 V	

1. The startup on communication line wakes the CPU which was made possible by an EXTI, this induces a delay before entering run mode.

3.2 ARM® Cortex®-M3 core with MPU

The ARM® Cortex®-M3 processor is the industry leading processor for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM® Cortex®-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The memory protection unit (MPU) improves system reliability by defining the memory attributes (such as read/write access permissions) for different memory regions. It provides up to eight different regions and an optional predefined background region.

Owing to its embedded ARM core, the STM32L151x6/8/B-A and STM32L152x6/8/B-A devices are compatible with all ARM tools and software.

3.4 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

- **Clock prescaler**: to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching**: clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management**: to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- **Master clock source**: three different clock sources can be used to drive the master clock:
  - 1-24 MHz high-speed external crystal (HSE), that can supply a PLL
  - 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLL
  - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65.5 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz) with a consumption proportional to speed, down to 750 nA typical. When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.
- **Auxiliary clock source**: two ultra-low-power clock sources that can be used to drive the LCD controller and the real-time clock:
  - 32.768 kHz low-speed external crystal (LSE)
  - 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.
- **RTC and LCD clock sources:** the LSI, LSE or HSE sources can be chosen to clock the RTC and the LCD, whatever the system clock.
- **USB clock source:** the embedded PLL has a dedicated 48 MHz clock output to supply the USB interface.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 2.1 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- **Clock security system (CSS):** this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled.
- **Clock-out capability (MCO: microcontroller clock output):** it outputs one of the internal clocks for external use by the application.

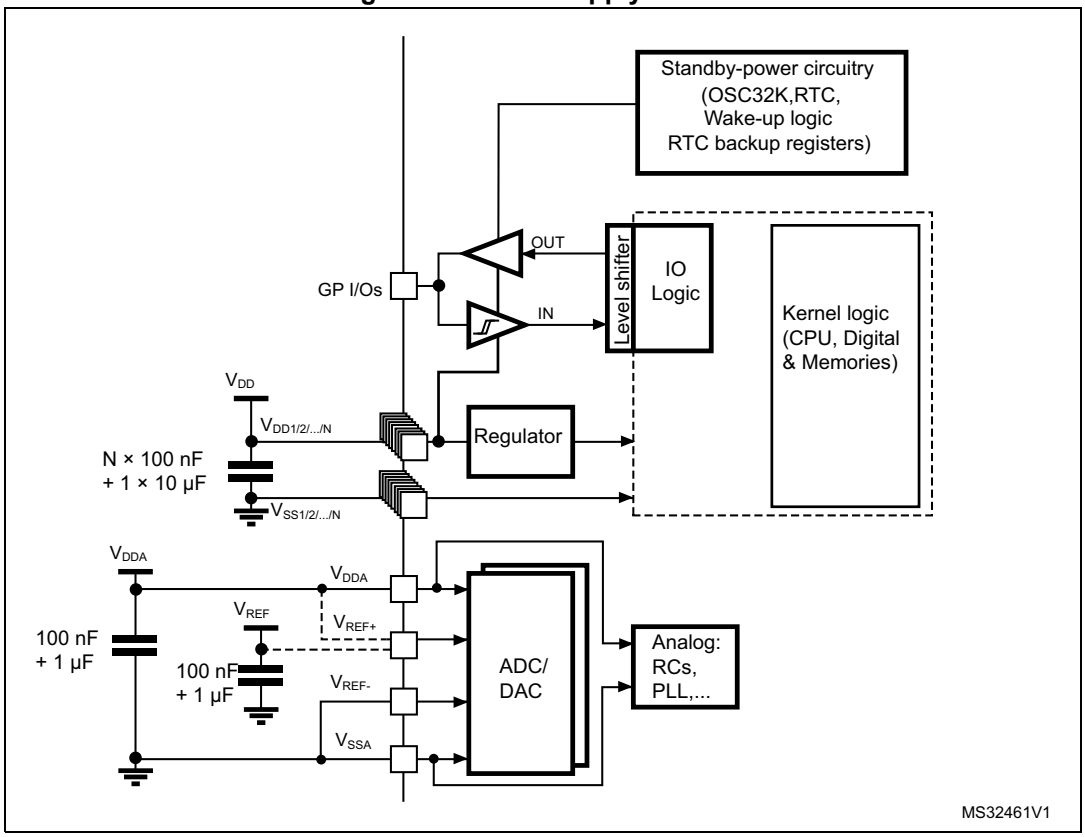
Several prescalers allow the configuration of the AHB frequency, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.

Table 9. STM32L151x6/8/B-A and STM32L152x6/8/B-A pin definitions (continued)

Pins					Pin name	Pin type(1)	I/O structure	Main function(2) (after reset)	Pins functions	
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UFQFPN48					Alternate functions	Additional functions
67	41	D7	D11	29	PA8	I/O	FT	PA8	USART1_CK/MCO/ LCD_COM0	-
68	42	C7	D10	30	PA9	I/O	FT	PA9	USART1_TX/ LCD_COM1	-
69	43	C6	C12	31	PA10	I/O	FT	PA10	USART1_RX/ LCD_COM2	-
70	44	C8	B12	32	PA11	I/O	FT	PA11	USART1_CTS/ SPI1_MISO	USB_DM
71	45	B8	A12	33	PA12	I/O	FT	PA12	USART1_RTS/ SPI1_MOSI	USB_DP
72	46	A8	A11	34	PA13	I/O	FT	JTMS-SWDIO	JTMS-SWDIO	-
73	-	-	C11	-	PH2	I/O	FT	PH2	-	-
74	47	D5	F11	35	V_{SS_2}	S	-	V_{SS_2}	-	-
75	48	E5	G11	36	V_{DD_2}	S	-	V_{DD_2}	-	-
76	49	A7	A10	37	PA14	I/O	FT	JTCK-SWCLK	JCTK-SWCLK	-
77	50	A6	A9	38	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/PA15/ SPI1_NSS/ LCD_SEG17	-
78	51	B7	B11	-	PC10	I/O	FT	PC10	USART3_TX/ LCD_SEG28/ LCD_SEG40/ LCD_COM4	-
79	52	B6	C10	-	PC11	I/O	FT	PC11	USART3_RX/ LCD_SEG29/ LCD_SEG41/ LCD_COM5	-
80	53	C5	B10	-	PC12	I/O	FT	PC12	USART3_CK/ LCD_SEG30/ LCD_SEG42/ LCD_COM6	-
81	-	-	C9	-	PD0	I/O	FT	PD0	SPI2_NSS/TIM9_CH1	-

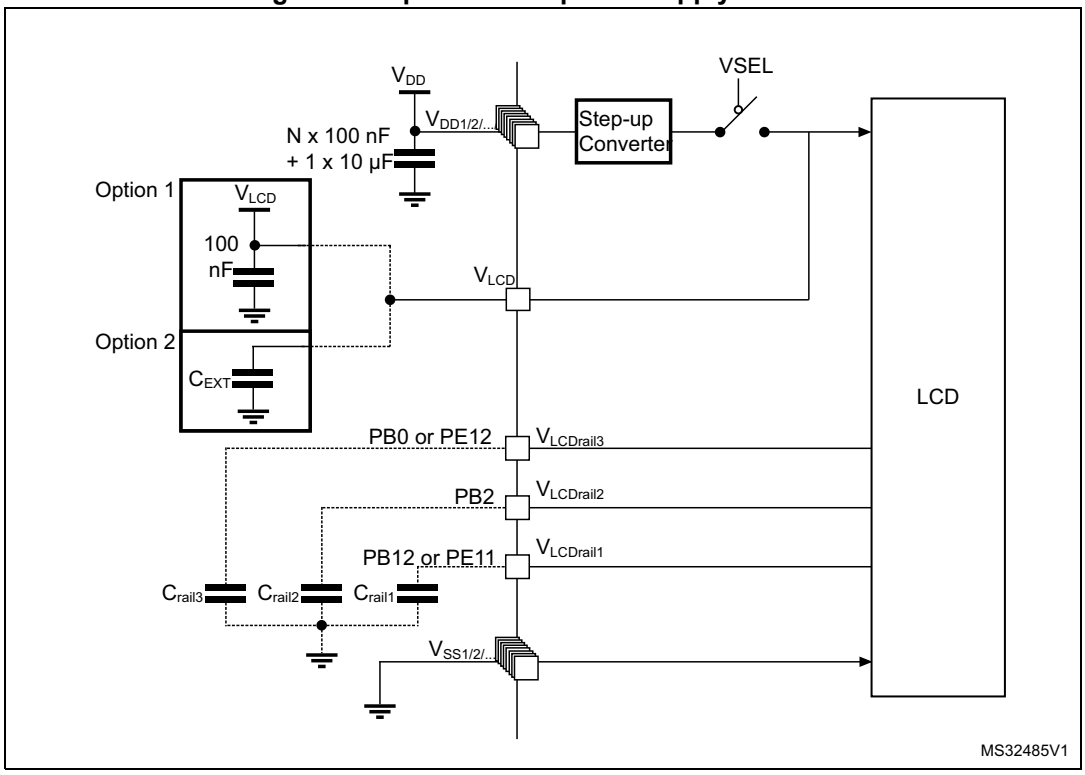
6.1.6 Power supply scheme

Figure 12. Power supply scheme



6.1.7 Optional LCD power supply scheme

Figure 13. Optional LCD power supply scheme



1. Option 1: LCD power supply is provided by a dedicated VLCD supply source, VSEL switch is open.
2. Option 2: LCD power supply is provided by the internal step-up converter, VSEL switch is closed, an external capacitance is needed for correct behavior of this converter.

6.1.8 Current consumption measurement

Figure 14. Current consumption measurement scheme

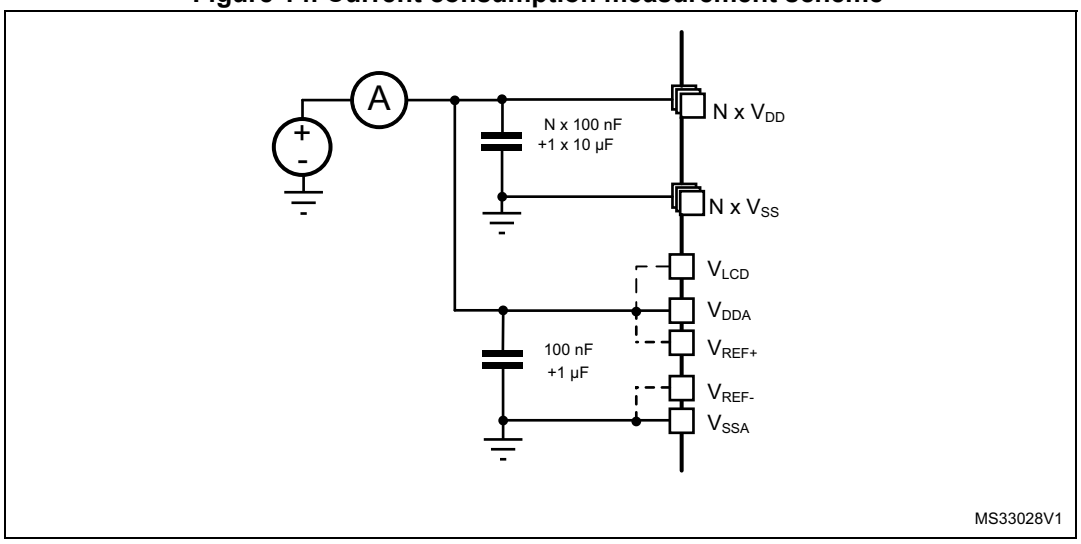


Table 15. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BOR0}	Brown-out reset threshold 0	Falling edge	1.67	1.7	1.74	V
		Rising edge	1.69	1.76	1.8	
V_{BOR1}	Brown-out reset threshold 1	Falling edge	1.87	1.93	1.97	
		Rising edge	1.96	2.03	2.07	
V_{BOR2}	Brown-out reset threshold 2	Falling edge	2.22	2.30	2.35	
		Rising edge	2.31	2.41	2.44	
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.45	2.55	2.60	
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.68	2.8	2.85	
		Rising edge	2.78	2.9	2.95	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	V
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization.
2. Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

Table 20. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	50	155	µA
				2 MHz	78.5	235	
				4 MHz	140	370(3)	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	165	375	
				8 MHz	310	530	
				16 MHz	590	1000	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	350	615	
				16 MHz	680	1200	
				32 MHz	1600	2350	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	640	970	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	1600	2350	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	65 kHz	19	60	
		MSI clock, 524 kHz		524 kHz	33	90	
		MSI clock, 4.2 MHz		4.2 MHz	145	210	
	Supply current in Sleep mode, Flash ON	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	60.5	145	µA
				2 MHz	89.5	225	
				4 MHz	150	360	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	180	370	
				8 MHz	320	490	
				16 MHz	605	895	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	380	565	
				16 MHz	695	1070	
				32 MHz	1600	2200	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	650	970	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	1600	2320	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2V VOS[1:0] = 11	65 kHz	29.5	65	
		MSI clock, 524 kHz		524 kHz	44	80	
		MSI clock, 4.2 MHz		4.2 MHz	155	220	

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register)
3. Guaranteed by test in production.

Table 23. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions			Typ(1)	Max (1)(2)	Unit
I_{DD} (Stop with RTC)	Supply current in Stop mode with RTC enabled	RTC clocked by LSI, regulator in LP mode, HSI and HSE OFF (no independent watchdog)	LCD OFF	T_A = -40°C to 25°C V_{DD} = 1.8 V	1.13	-	µA
				T_A = -40°C to 25°C	1.38	4	
				T_A = 55°C	1.70	6	
				T_A= 85°C	3.30	10	
				T_A = 105°C	7.80	23	
			LCD ON (static duty)(3)	T_A = -40°C to 25°C	1.50	6	
				T_A = 55°C	1.80	7	
				T_A= 85°C	3.45	12	
				T_A = 105°C	8.02	27	
			LCD ON (1/8 duty)(4)	T_A = -40°C to 25°C	3.80	10	
				T_A = 55°C	4.30	11	
				T_A= 85°C	6.10	16	
				T_A = 105°C	10.8	44	
		RTC clocked by LSE external clock (32.768 kHz), regulator in LP mode, HSI and HSE OFF (no independent watchdog)	LCD OFF	T_A = -40°C to 25°C	1.50	-	
				T_A = 55°C	1.90	-	
				T_A= 85°C	3.65	-	
				T_A = 105°C	8.25	-	
			LCD ON (static duty)(3)	T_A = -40°C to 25°C	1.60	-	
				T_A = 55°C	2.05	-	
				T_A= 85°C	3.75	-	
				T_A = 105°C	8.40	-	
			LCD ON (1/8 duty)(4)	T_A = -40°C to 25°C	3.90	-	
				T_A = 55°C	4.55	-	
				T_A= 85°C	6.35	-	
				T_A = 105°C	11.10	-	
		RTC clocked by LSE (no independent watchdog)(5)	LCD OFF	T_A = -40°C to 25°C V_{DD} = 1.8 V	1.23	-	
				T_A = -40°C to 25°C V_{DD} = 3.0 V	1.50	-	
				T_A = -40°C to 25°C V_{DD} = 3.6 V	1.75	-	

6.3.7 Internal clock source characteristics

The parameters given in the following table are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

High-speed internal (HSI) RC oscillator

Table 31. HSI oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	V_{DD} = 3.0 V	-	16	-	MHz
$TRIM^{(1)(2)}$	HSI user-trimmed resolution	Trimming code is not a multiple of 16	-	±0.4	0.7	%
		Trimming code is a multiple of 16	-	-	±1.5	%
$ACC_{HSI}^{(2)}$	Accuracy of the factory-calibrated HSI oscillator	V_{DDA} = 3.0 V, T_A = 25 °C	-1(3)	-	1(3)	%
		V_{DDA} = 3.0 V, T_A = 0 to 55 °C	-1.5	-	1.5	%
		V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 105 °C	-4	-	2	%
		V_{DDA} = 1.65 V to 3.6 V T_A = -40 to 105 °C	-4	-	3	%
$t_{SU(HSI)}^{(2)}$	HSI oscillator startup time	-	-	3.7	6	µs
$I_{DD(HSI)}^{(2)}$	HSI oscillator power consumption	-	-	100	140	µA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Low-speed internal (LSI) RC oscillator

Table 32. LSI oscillator characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$f_{LSI}^{(1)}$	LSI frequency	26	38	56	kHz
$D_{LSI}^{(2)}$	LSI oscillator frequency drift 0°C ≤T_A ≤85°C	-10	-	4	%
$t_{su(LSI)}^{(3)}$	LSI oscillator startup time	-	-	200	µs
$I_{DD(LSI)}^{(3)}$	LSI oscillator power consumption	-	400	510	nA

1. Guaranteed by test in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design.

Multi-speed internal (MSI) RC oscillator

Table 33. MSI oscillator characteristics

Symbol	Parameter	Condition	Typ	Max	Unit
f_{MSI}	Frequency after factory calibration, done at V_{DD}= 3.3 V and T_A = 25 °C	MSI range 0	65.5	-	kHz
		MSI range 1	131	-	
		MSI range 2	262	-	
		MSI range 3	524	-	
		MSI range 4	1.05	-	MHz
		MSI range 5	2.1	-	
		MSI range 6	4.2	-	
ACC_{MSI}	Frequency error after factory calibration	-	±0.5	-	%
$D_{TEMP(MSI)}$(1)	MSI oscillator frequency drift 0 °C ≤T_A ≤105 °C	-	±3	-	%
$D_{VOLT(MSI)}$(1)	MSI oscillator frequency drift 1.65 V ≤V_{DD} ≤3.6 V, T_A = 25 °C	-	-	2.5	%/V
$I_{DD(MSI)}$(2)	MSI oscillator power consumption	MSI range 0	0.75	-	µA
		MSI range 1	1	-	
		MSI range 2	1.5	-	
		MSI range 3	2.5	-	
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	-	
$t_{SU(MSI)}$	MSI oscillator startup time	MSI range 0	30	-	µs
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
		MSI range 4	6	-	
		MSI range 5	5	-	
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	

6.3.13 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 43* are derived from tests performed under conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 43. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage	TC and FT I/O	-	-	0.3 V_{DD}(1)(2)	V
		BOOT0	-		0.14 V_{DD}(2)	
V_{IH}	Input high level voltage	TC I/O	0.45 V_{DD}+0.38(2)	-	-	
		FT I/O	0.39 V_{DD}+0.59(2)	-	-	
		BOOT0	0.15 V_{DD}+0.56(2)	-	-	
V_{hys}	I/O Schmitt trigger voltage hysteresis(2)	TC and FT I/O	-	10% V_{DD}(3)	-	
		BOOT0	-	0.01	-	
I_{lkg}	Input leakage current(4)	$V_{SS} \le V_{IN} \le V_{DD}$ I/Os with LCD	-	-	±50	nA
		$V_{SS} \le V_{IN} \le V_{DD}$ I/Os with analog switches	-	-	±50	
		$V_{SS} \le V_{IN} \le V_{DD}$ I/Os with analog switches and LCD	-	-	±50	
		$V_{SS} \le V_{IN} \le V_{DD}$ I/Os with USB	-	-	±250	
		$V_{SS} \le V_{IN} \le V_{DD}$ TC and FT I/O	-	-	±50	
		FT I/O $V_{DD} \le V_{IN} \le 5V$	-	-	±10	uA
R_{PU}	Weak pull-up equivalent resistor(5)(1)	$V_{IN} = V_{SS}$	30	45	60	kΩ
R_{PD}	Weak pull-down equivalent resistor(5)	$V_{IN} = V_{DD}$	30	45	60	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Guaranteed by test in production.
2. Guaranteed by design.
3. With a minimum of 200 mV.
4. The max. value may be exceeded if negative current is injected on adjacent pins.
5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±20 mA (with the non-standard V_{OL}/V_{OH} specifications given in *Table 44*.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 12*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 12*).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 44* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

Table 44. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL} (1)(2)	Output low level voltage for an I/O pin	I_{IO} = 8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH} (3)(2)	Output high level voltage for an I/O pin		V_{DD}-0.4	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = 4 mA 1.65 V < V_{DD} < 2.7 V	-	0.45	
V_{OH} (3)(4)	Output high level voltage for an I/O pin		V_{DD}-0.45	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = 15 mA 2.7 V < V_{DD} < 3.6 V	-	1.3	
V_{OH} (3)(4)	Output high level voltage for an I/O pin		V_{DD}-1.3	-	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 12* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. Guaranteed by test in production.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 12* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.
4. Guaranteed by characterization results.

Figure 22. SPI timing diagram - slave mode and CPHA = 0

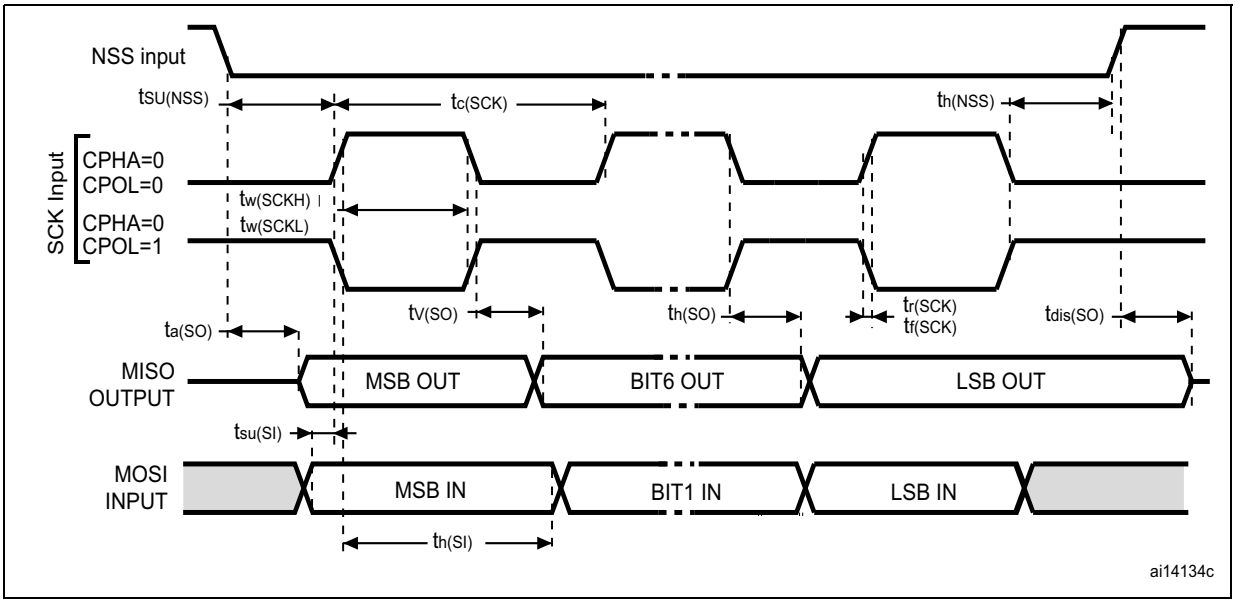
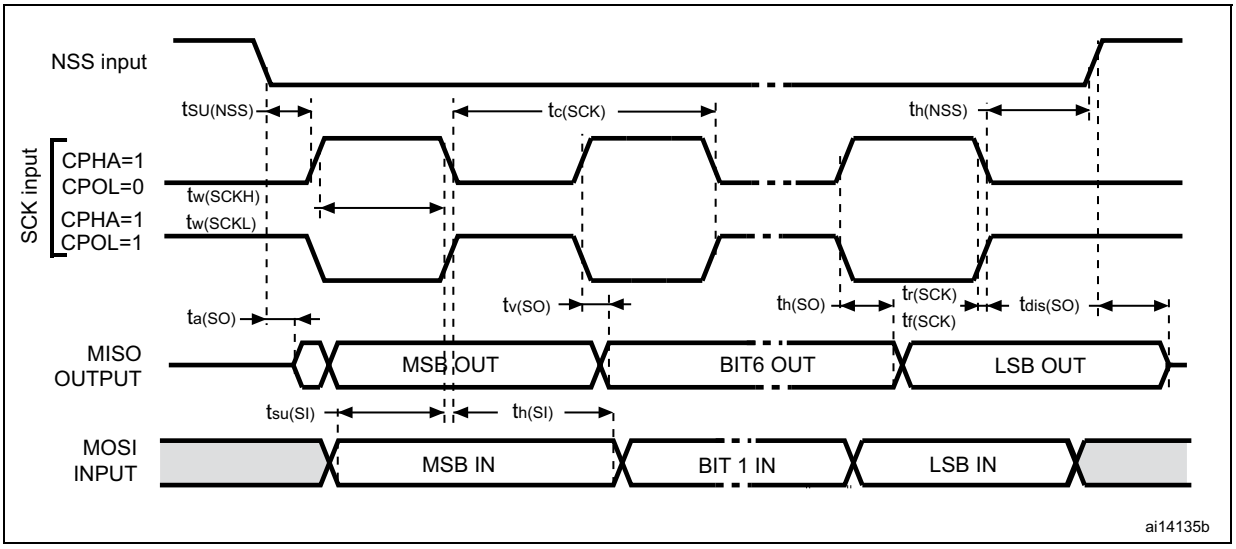
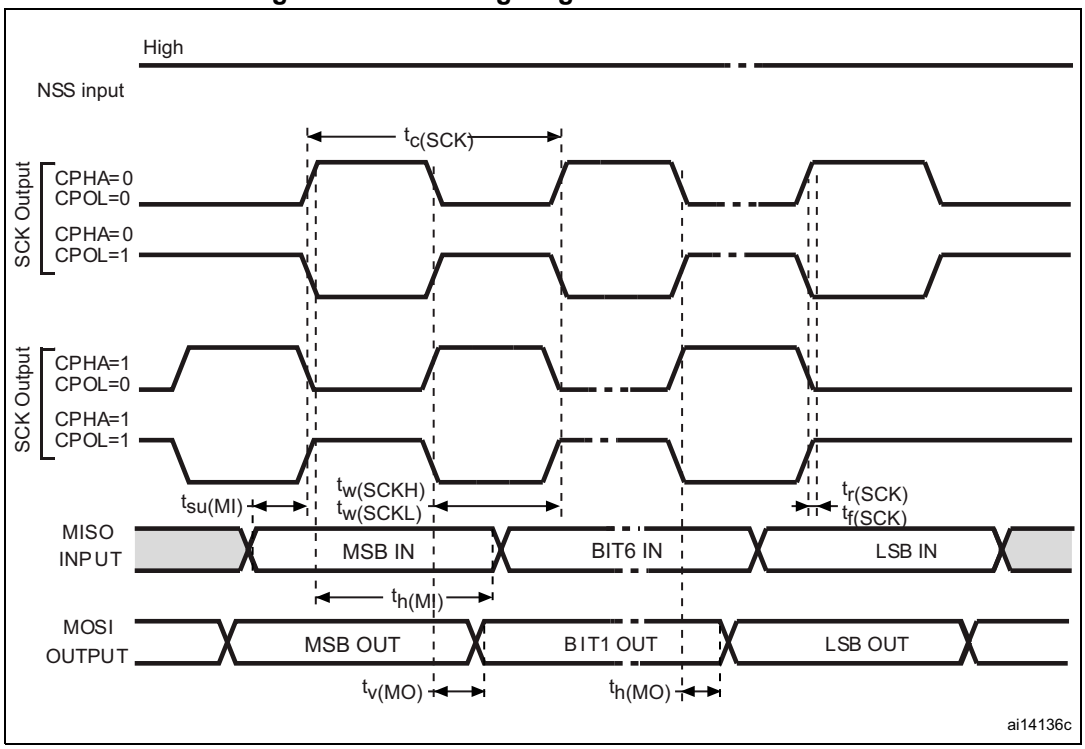


Figure 23. SPI timing diagram - slave mode and CPHA = 1(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Figure 24. SPI timing diagram - master mode(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

USB characteristics

The USB interface is USB-IF certified (full speed).

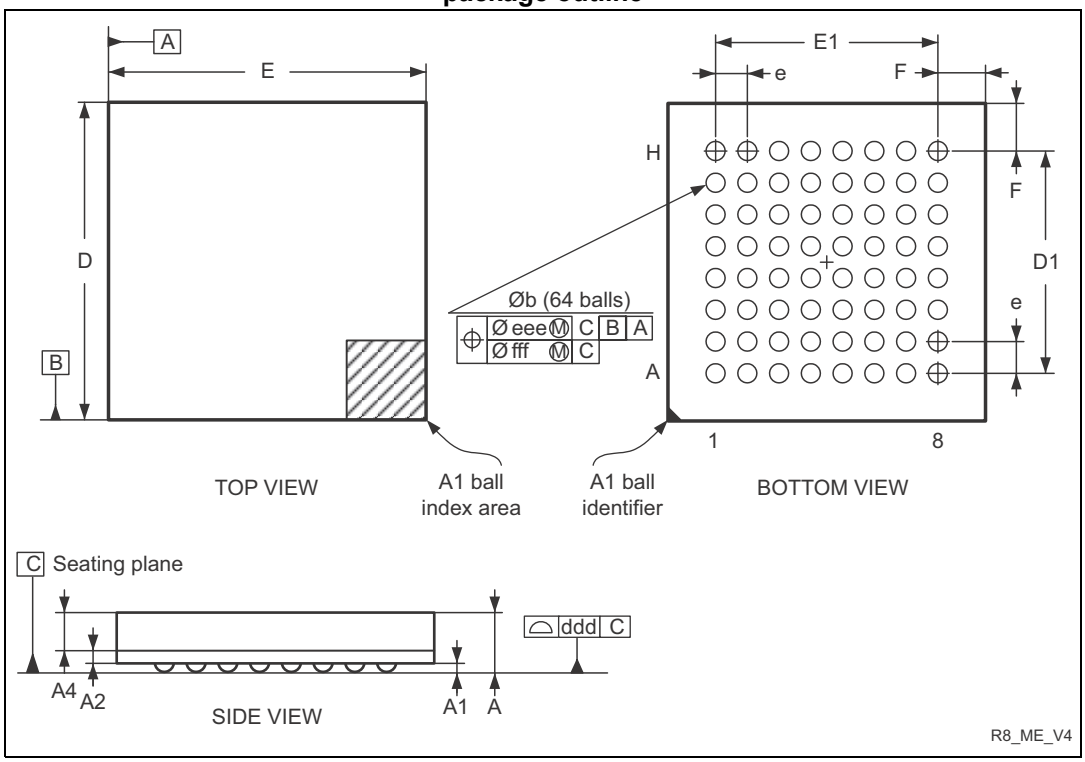
Table 51. USB startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB transceiver startup time	1	µs

1. Guaranteed by design.

7.6 TFBGA64 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package information

Figure 45. TFBGA64 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package outline



1. Drawing is not to scale.

Table 70. TFBGA64 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.200	-	-	0.0472
A1	0.150	-	-	0.0059	-	-
A2	-	0.200	-	-	0.0079	-
A4	-	-	0.600	-	-	0.0236
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	-	3.500	-	-	0.1378	-
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	-	3.500	-	-	0.1378	-
e	-	0.500	-	-	0.0197	-
F	-	0.750	-	-	0.0295	-

8 Ordering information

Table 73. Ordering information scheme

Example: STM32 L 152 R B T 6 A D TR

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

L = Low-power

Device subfamily

151: Devices without LCD

152: Devices with LCD

Pin count

C = 48 pins

R = 64 pins

V = 100 pins

Flash memory size

6 = 32 Kbytes of Flash memory

8 = 64 Kbytes of Flash memory

B = 128 Kbytes of Flash memory

Package

H = BGA

T = LQFP

U = UFQFPN

Temperature range

6 = Industrial temperature range, –40 to 85 °C

7 = Industrial temperature range, –40 to 105 °C

Options

A = device generation A

No character = VDD range: 1.8 to 3.6 V and BOR enabled

D = VDD range: 1.65 to 3.6 V and BOR disabled

Packing

TR = tape and reel

No character = tray or tube

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.